

## BTA208X-1000C

双向可控硅  
TRIAC版本号  
201603-A

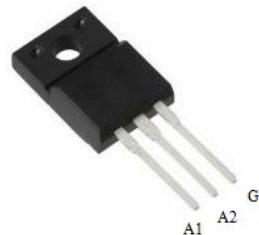
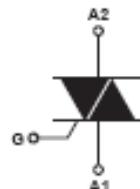
## 产品概述 GENERAL DESCRIPTION

BTA208X-1000C 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

BTA208X-1000C Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

## 主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I <sub>T(RMS)</sub>	8	A
V <sub>DRM/V<sub>RRM</sub></sub>	1000	V
I <sub>GT(HI)</sub>	≤35	mA
V <sub>ISO</sub>	2000	V



## 产品特性 FEATURES

- dv/dt高
- 通态压降低
- Rohs环保产品
- Highly dv/dt
- Low on-state voltage
- Rohs Products

## 应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

## 极限值(除非另有规定, $T_j=25^\circ\text{C}$ ) ABSOLUTE RATINGS

( $T_j=25^\circ\text{C}$ ,unless otherwise specified)

符号 Symbol	参数 Parameter			数值 Value	单位 Unit
$I_{T(\text{RMS})}$	RMS 通态电流 RMS on-state current (full sine wave)			8	A
$I_{TSM}$	通态峰值浪涌电流 Non repetitive surge peak on-state current			80	A
$I^2t$	$I^2t$ 耗散值 $I^2t$ value for fusing			36	$\text{A}^2\text{s}$
$di/dt$	通态电流上升值 Critical rate of rise of on-state current			50	$\text{A}/\mu\text{s}$
$I_{GM}$	门极峰值电流 Peak gate current			4	A
$P_{G(\text{AV})}$	平均门极耗散功率 Average gate power dissipation			1	W
$T_{stg}$	贮存结温范围 Storage junction temperature range			-40~+150	$^\circ\text{C}$
$T_j$	工作结温范围 Operating junction temperature range			-40~+150	$^\circ\text{C}$

## 电参数(除非另有规定, $T_j=25^\circ\text{C}$ ) ELECTRICAL CHARACTERISTICS

( $T_j=25^\circ\text{C}$ ,unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value			单位 Unit	测试条件 Test Conditions	
		Min.	Typ.	Max.			
触发电流 Gate trigger current	$I_{GT}$	I ~ III	10	-	35	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
触发电压 Gate trigger voltage	$V_{GT}$	I ~ III	$\leq 1.5$			V	$V_D=12\text{V}, I_T=0.1\text{A}$
维持电流 Holding current	$I_H$		-	-	50	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
擎住电流 Latching current	$I_L$		-	-	60	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
电压上升率 Rise of off- state voltage	$dv/dt$		500	-	-	V/ $\mu\text{s}$	$V_D=67\% V_{DRM}$
通态压降 Peak on-state voltage	$V_{TM}$		$\leq 1.55$			V	$I_T=11\text{A}$
断态漏电流 Peak repetitive forward blocking current	$I_{DRM}$		$\leq 5$			$\mu\text{A}$	$V_{RRM}=V_{DRM}, T_j = 25^\circ\text{C}$
	$I_{RRM}$		$\leq 3.1$			mA	$V_{RRM}=V_{DRM}, T_j = 150^\circ\text{C}$

## 热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
$R_{th(j-c)}$	Junction to case(AC)	1.7	K/W
$R_{th(j-a)}$	Junction to ambient	60	K/W

## 特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系

Fig.1. Maximum Power Dissipation Versus RMS On-state current

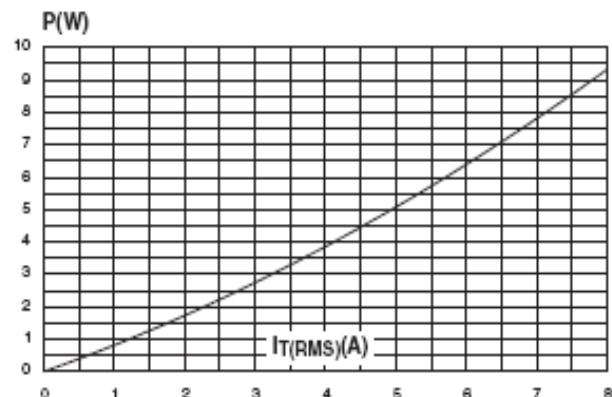


图3 通态特性

Fig.3. On-State Characteristics

图2 RMS通态电流与Tc温度关系

Fig.2. RMS On-state Current Versus T<sub>c</sub>

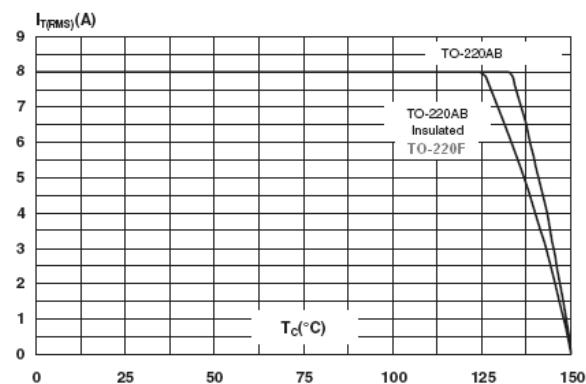


图4 通态浪涌峰值电流与周期数关系

Fig.4. Surge Peak On-state Current Versus Number Cycles

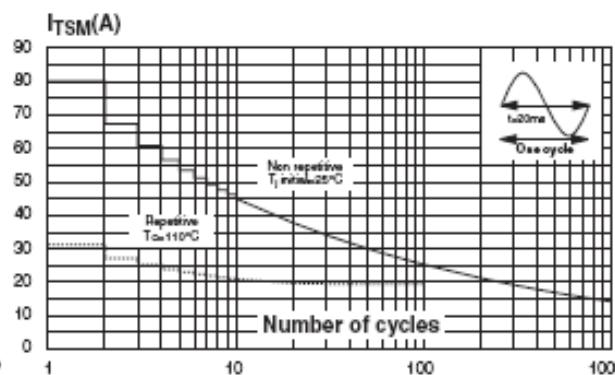
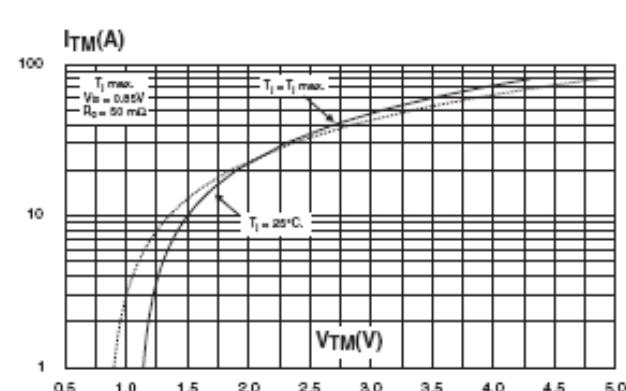
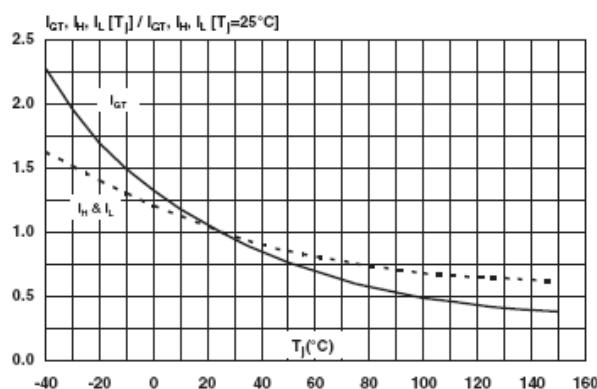


图5 I<sub>GT</sub>、I<sub>H</sub>、I<sub>L</sub>相对值（相对于25°C）与结温关系

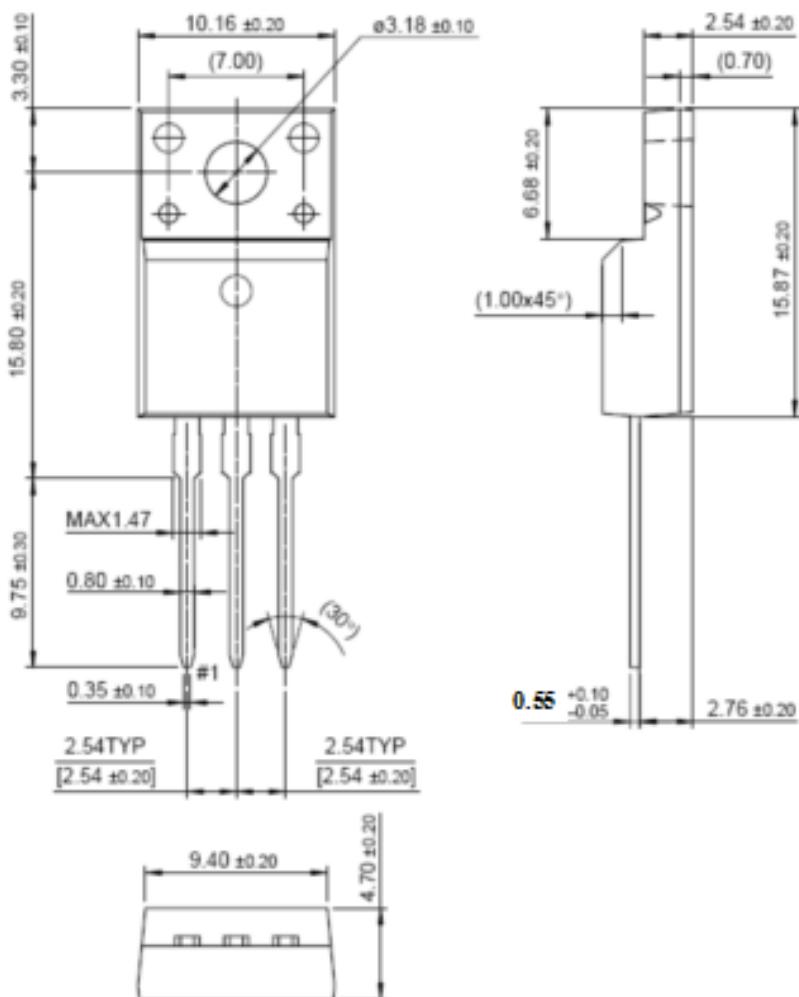
Fig.5. Relative Variation Of Gate Trigger Current

, Holding Current And Latching Current Versus Junction Temperature (Typical Value)



## 封装尺寸 PACKAGE MECHANICAL DATA

TO-220F



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